

Amendments to the Claims:

Status of Claims:

Claims 19-35 are presented for examination.

Claim 36 is added by the present amendment.

Claims 19, 28, 33-35 are canceled by the present amendment. Claims 1-18 were previously canceled.

Claims 23 and 29 are in independent form.

1-18. (Canceled)

19. (Canceled).

20. (Currently Amended) The method of Claim ~~[[19]]~~ 23 further comprising:
applying a barrier layer to the thinfilm structure after forming the break trench structure and before abrasively machining the substrate.

21. (Currently Amended) The method of Claim ~~[[19]]~~ 23 wherein said fabricating the thinfilm structure includes fabricating the thinfilm structure on said first surface of the substrate.

22. (Currently Amended) The method of Claim ~~[[19]]~~ 23 wherein said forming a break trench structure includes anisotropically etching the trench during a wet etch process.

23. (Currently Amended) A ~~The method of Claim 19, further including fabricating a fluid ejection device, comprising:~~

fabricating a thinfilm structure on a device substrate;

forming a peripheral break trench structure in a first surface of the substrate circumscribing a region in which a feed slot is to be formed through the substrate;

forming a guide break trench in said first surface within the peripheral break trench structure; and

subsequently abrasively machining the substrate from a second surface of the substrate to the break trench structure to form the feed slot.

24. (Original) The method of Claim 23, wherein said guide break trench structure is formed to a depth deeper than a depth of said peripheral break trench structure.

25. (Original) The method of Claim 24, wherein the guide break trench structure is formed with a trench width greater than a width of said peripheral break trench structure.

26. (Currently Amended) The method of Claim ~~[[19]]~~ 23, wherein the substrate is a silicon substrate, and wherein said forming a break trench structure includes:

etching the silicon substrate with a TMAH (Tetra Methyl Ammonium Hydroxide) wet etch process.

27. (Currently Amended) A fluid ejection device produced by the method of Claim ~~[[19]]~~ 23.

28. (Canceled).

29. (Currently Amended) ~~A The~~ method of Claim 28, further fabricating a fluid ejection device, comprising:

fabricating a thinfilm structure on a device substrate;

forming a break trench structure in a first surface of the substrate, said structure comprising a plurality of small break trenches arranged along a slot axis;

subsequently abrasively machining the substrate from a second surface of the substrate to the plurality of break trenches to form a plurality of small feed slots through the substrate; and

defining a plurality of small substrate islands in areas separating the small slots.

30. (Original) The method of Claim 29, wherein said defining a plurality of small substrate islands comprises:

forming a mask structure defining the islands;

etching the first surface through the mask structure to define the plurality of small substrate islands.

31. (Currently Amended) The method of Claim [[28]] 29, wherein said substrate is a silicon substrate, and wherein said forming a break trench structure includes:

etching the silicon substrate with a TMAH (Tetra Methyl Ammonium Hydroxide) wet etch process.

32. (Currently Amended) A fluid ejection device produced by the method of Claim [[28]] 29.

33-35. (Canceled).

36. (New) The method of claim 23 further comprising:

fabricating the thinfilm structure on the device substrate for a plurality of fluid ejection devices to be formed on the substrate, where the substrate is a wafer;

attaching an orifice plate structure for each of the fluid ejection devices to be formed on the wafer;

sawing the wafer to separate individual fluid ejection devices; and

attaching the fluid ejection devices to device circuitry on the wafer.